

# MSKSEMI 美森科

SEMICONDUCTOR



ESD



TVS



TSS



MOV



GDT



PLED

## AO3423

Product specification

**Features**

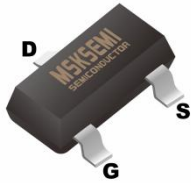
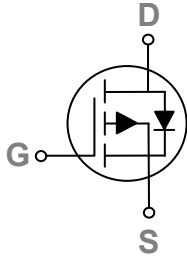

- -20V,-2.0A, RDS(ON) =95mΩ@VGS =-4.5V
- Improved dv/dt capability
- Fast switching
- Green Device Available

**Applications**

- Notebook
- Load Switch
- Hand-Held Instruments

BVDSS	RDSON	ID
-20V	95mΩ	-2.0A

**Reference News**

PACKAGE OUTLINE	PIN Configuration	Marking
 <p>SOT-23-3L</p>		

**Absolute Maximum Ratings Tc=25°C unless otherwise noted**

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-20	V
V <sub>GS</sub>	Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current – Continuous (T <sub>C</sub> =25°C)	-2.0	A
	Drain Current – Continuous (T <sub>C</sub> =100°C)	-1.6	A
I <sub>DM</sub>	Drain Current – Pulsed <sup>1</sup>	-8.0	A
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> =25°C)	1.56	W
	Power Dissipation – Derate above 25°C	0.012	W/°C
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

**Thermal Characteristics**

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction to ambient	---	80	°C/W

**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**
**Off Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B <sub>V</sub> DSS	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V , I <sub>D</sub> =-250uA	-20	---	---	V
ΔB <sub>V</sub> DSS/ΔT <sub>J</sub>	B <sub>V</sub> DSS Temperature Coefficient	Reference to 25°C , I <sub>D</sub> =-1mA	---	-0.01	---	V/°C
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =-20V , V <sub>GS</sub> =0V , T <sub>J</sub> =25°C	---	---	-1	uA
		V <sub>DS</sub> =-16V , V <sub>GS</sub> =0V , T <sub>J</sub> =125°C	---	---	-10	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±12V , V <sub>DS</sub> =0V	---	---	±100	nA

**On Characteristics**

R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-2.0A	---	95	120	mΩ
		V <sub>GS</sub> =-2.5V , I <sub>D</sub> =-1A	---	120	160	
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =-250uA	-0.4	-0.7	-1.1	V
ΔV <sub>GS(th)</sub>	V <sub>GS(th)</sub> Temperature Coefficient		---	3	---	mV/°C

**Dynamic and switching Characteristics**

Q <sub>g</sub>	Total Gate Charge <sup>2, 3</sup>	V <sub>DS</sub> =-10V , V <sub>GS</sub> =-4.5V , I <sub>D</sub> =-1A	---	3.0	---	nC
Q <sub>gs</sub>	Gate-Source Charge <sup>2, 3</sup>		---	0.5	---	
Q <sub>gd</sub>	Gate-Drain Charge <sup>2, 3</sup>		---	0.8	---	
T <sub>d(on)</sub>	Turn-On Delay Time <sup>2, 3</sup>	V <sub>DD</sub> =-10V , V <sub>GS</sub> =-4.5V , R <sub>G</sub> =3Ω I <sub>D</sub> =-1A	---	10	---	nS
T <sub>r</sub>	Rise Time <sup>2, 3</sup>		---	5.5	---	
T <sub>d(off)</sub>	Turn-Off Delay Time <sup>2, 3</sup>		---	20	---	
T <sub>f</sub>	Fall Time <sup>2, 3</sup>		---	6.5	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =-10V , V <sub>GS</sub> =0V , F=1MHz	---	180	---	pF
C <sub>oss</sub>	Output Capacitance		---	35	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	25	---	

**Drain-Source Diode Characteristics and Maximum Ratings**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current	V <sub>G</sub> =V <sub>D</sub> =0V , Force Current	---	---	-2.0	A
I <sub>SM</sub>	Pulsed Source Current		---	---	-4.0	A
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V , I <sub>S</sub> =-1A , T <sub>J</sub> =25°C	---	---	-1.2	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%.
3. Essentially independent of operating temperature.

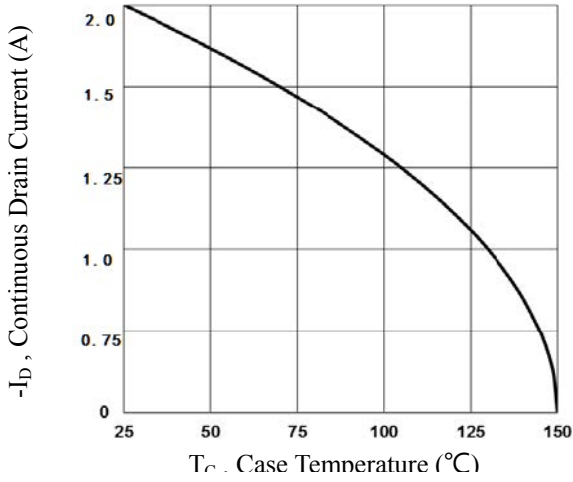


Fig.1 Continuous Drain Current vs.  $T_C$

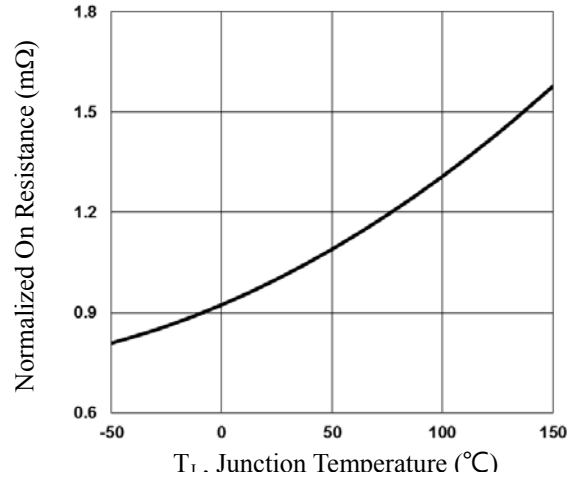


Fig.2 Normalized  $R_{DS(on)}$  vs.  $T_J$

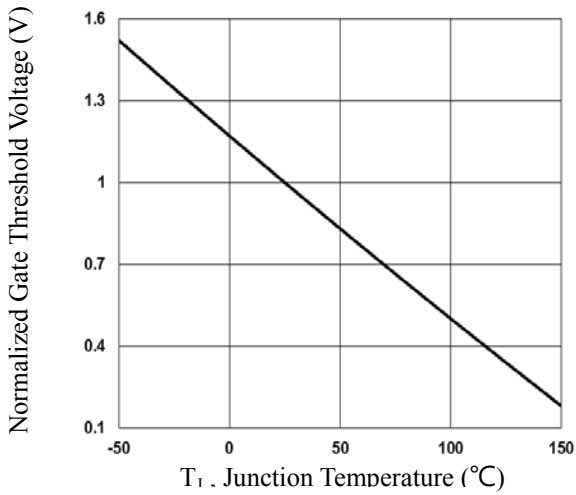


Fig.3 Normalized  $V_{th}$  vs.  $T_J$

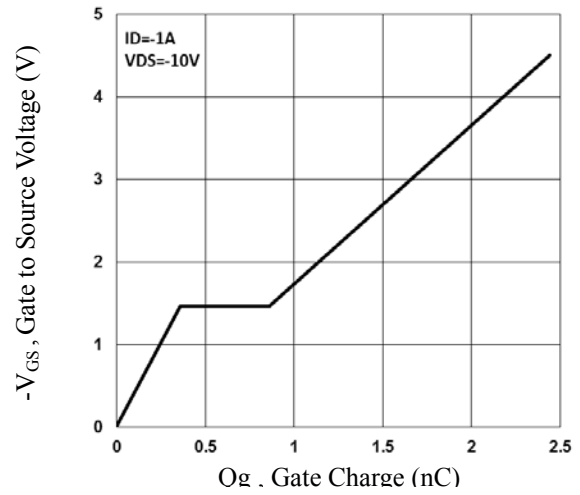


Fig.4 Gate Charge Waveform

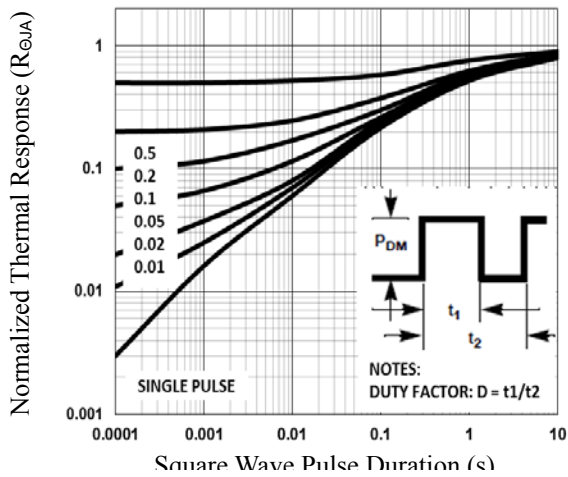


Fig.5 Normalized Transient Impedance

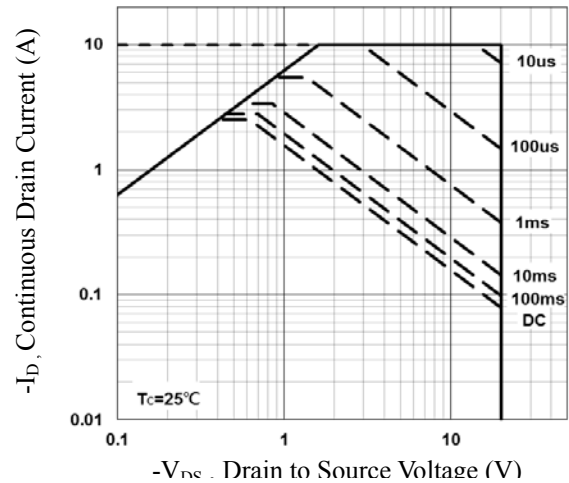


Fig.6 Maximum Safe Operation Area

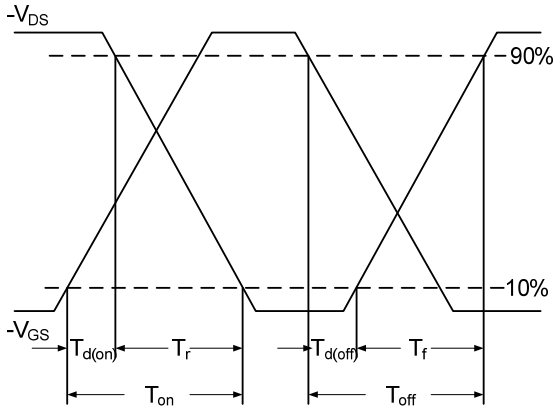


Fig.7 Switching Time Waveform

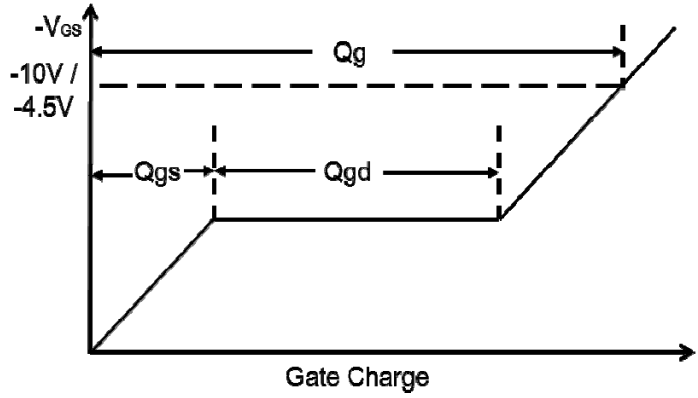
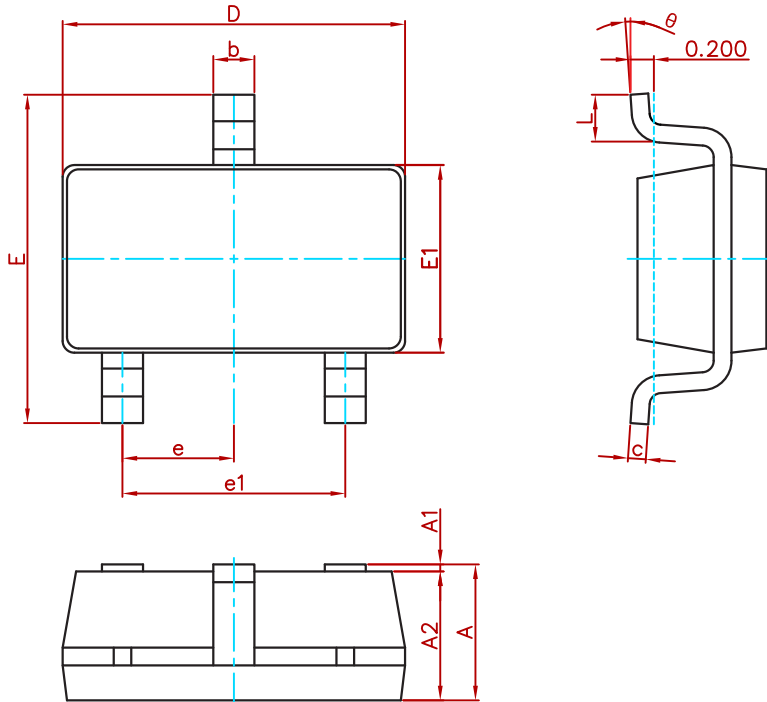


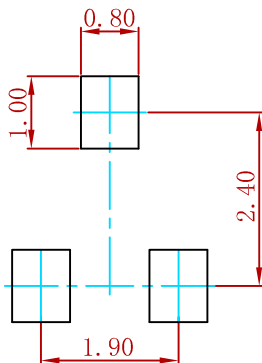
Fig.8 Gate Charge Waveform

**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
$\theta$	0°	8°	0°	8°

**Suuggested Pad Layout**



Note:  
 1. Controlling dimension: in millimeters.  
 2. General tolerance:  $\pm 0.05$ mm.  
 3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
AO3423	SOT-23-3L	3000

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